

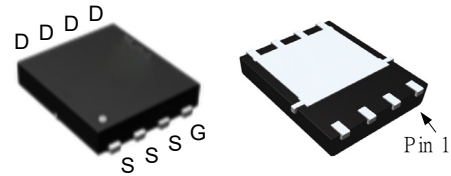
Features

- 60V/-60A
 $R_{DS(ON)}=10\text{m}\Omega(\text{typ.})@V_{GS}=-10\text{V}$
 $R_{DS(ON)}=11\text{m}\Omega(\text{typ.})@V_{GS}=-4.5\text{V}$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)

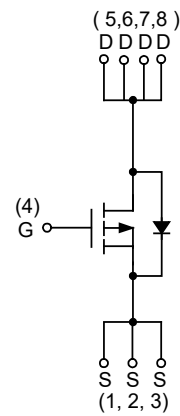
Applications

- DC/DC Converter.
- Power Management.
- Load Switch.
- Portable Equipment and Battery Powered Systems.

Pin Description



DFN5x6A-8_EP



P-Channel MOSFET

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-60	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	-28	A
I _D	Continuous Drain Current	T _C =25°C	-60	A
		T _C =100°C	-36	
I _{DM}	Pulsed Drain Current	T _C =25°C	-224 ^a	
P _D	Maximum Power Dissipation	T _C =25°C	89.3	W
		T _C =100°C	35.7	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	1.4	°C/W
I _D	Continuous Drain Current	T _A =25°C	-9	A
		T _A =70°C	-7	
P _D	Maximum Power Dissipation	T _A =25°C	2.27	W
		T _A =70°C	1.45	
R _{θJA}	Thermal Resistance-Junction to Ambient	Steady State	55	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	-28	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	196	mJ

Note a : Pulse width limited by maximum junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

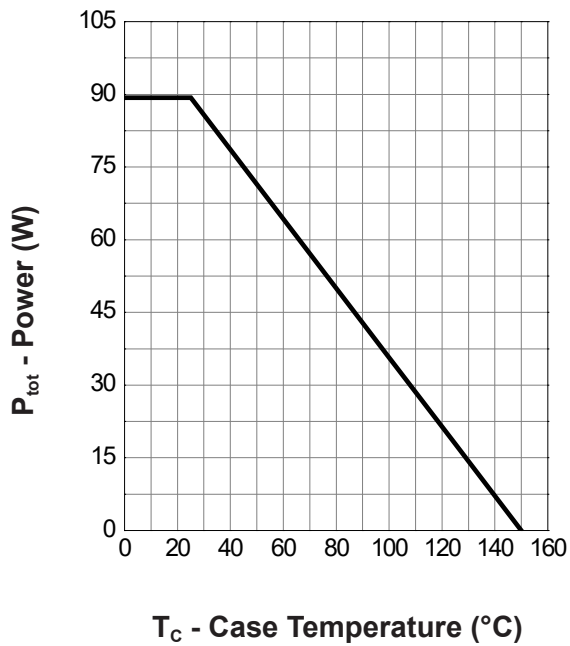
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-48V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.1	-1.6	-2.1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^c	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-25A	-	10	14	mΩ
		V _{GS} =-4.5V, I _{DS} =-25A	-	11	15	
Diode Characteristics						
V _{SD} ^c	Diode Forward Voltage	I _{SD} =-12A, V _{GS} =0V	-	-0.8	-1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-25A, dI _{SD} /dt=100A/μs	-	39	-	ns
Q _{rr}	Reverse Recovery Charge		-	62	-	nC
Dynamic Characteristics ^d						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, Frequency=1.0MHz	-	4800	6240	pF
C _{oss}	Output Capacitance		-	350	-	
C _{rss}	Reverse Transfer Capacitance		-	185	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-30V, R _L =30Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	23	41	ns
t _r	Turn-on Rise Time		-	18	32	
t _{d(OFF)}	Turn-off Delay Time		-	115	207	
t _f	Turn-off Fall Time		-	47	85	
Gate Charge Characteristics ^d						
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-10V, I _{DS} =-25A	-	90	126	nC
Q _{gs}	Gate-Source Charge		-	19	-	
Q _{gd}	Gate-Drain Charge		-	24	-	

Note c : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

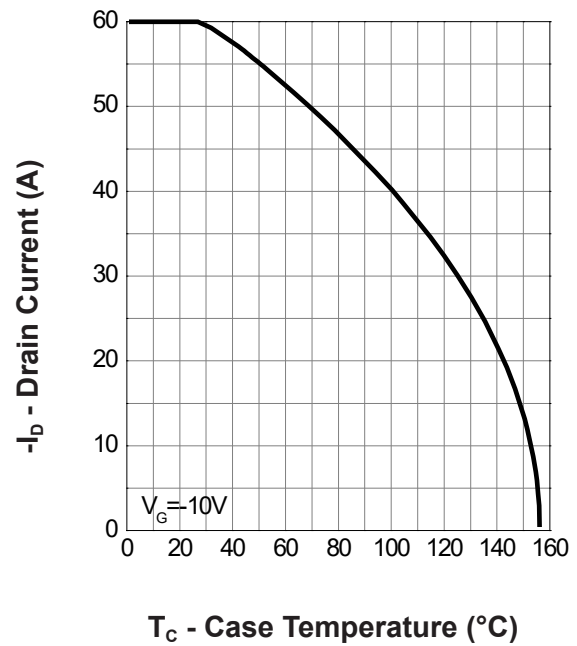
Note d : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

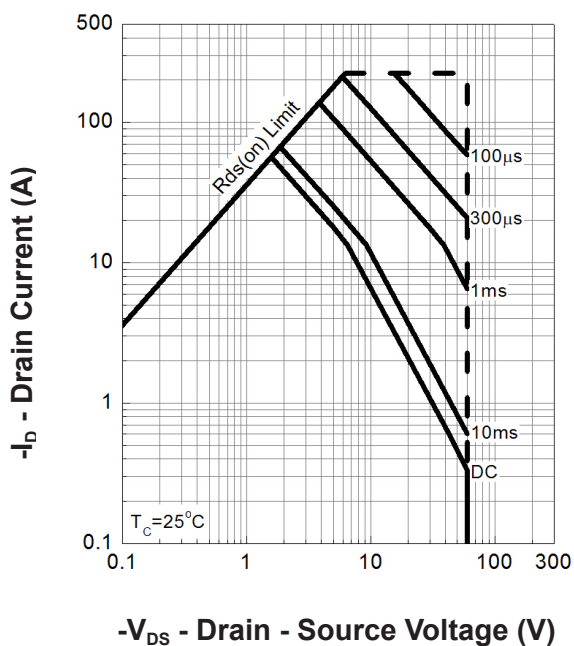
Power Dissipation



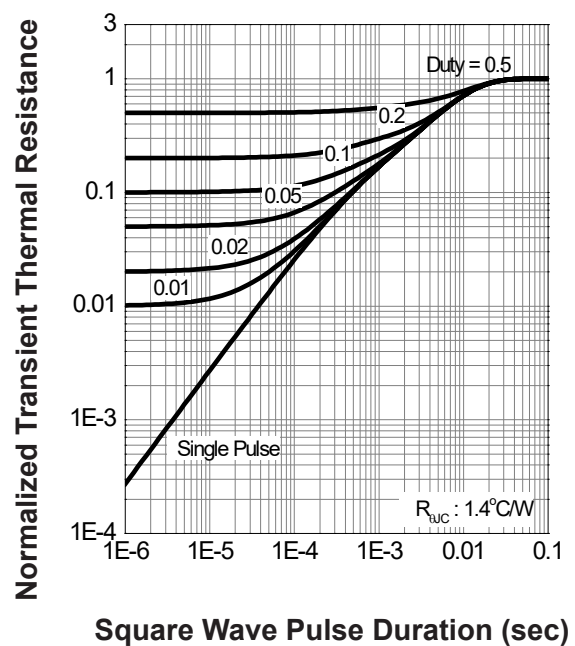
Drain Current



Safe Operation Area

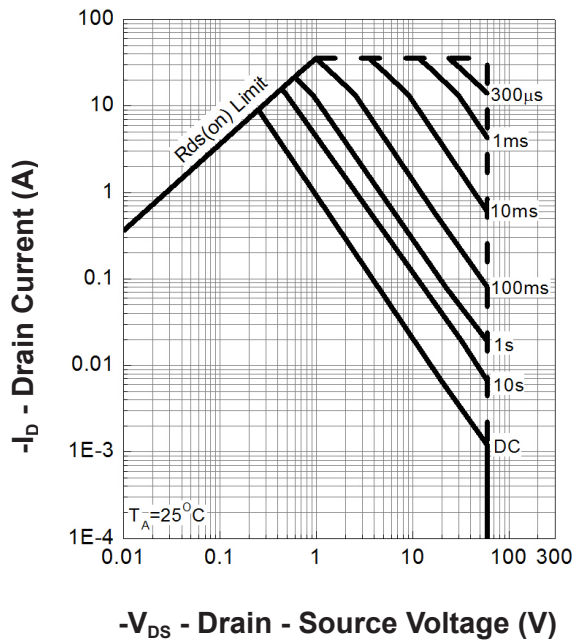


Thermal Transient Impedance

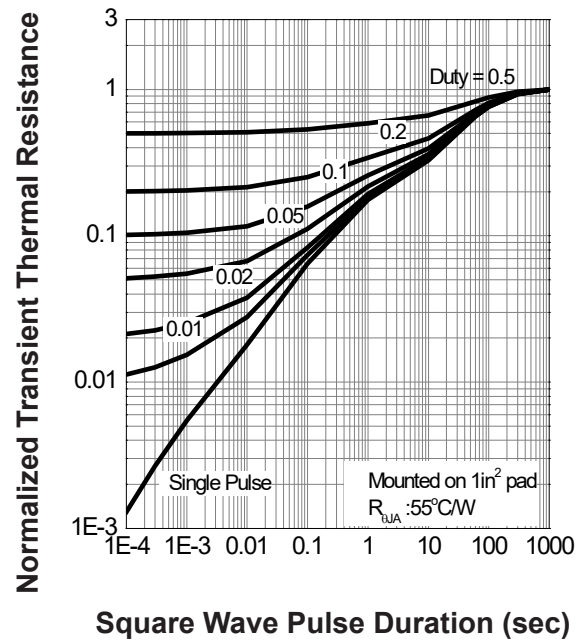


Typical Operating Characteristics(Cont.)

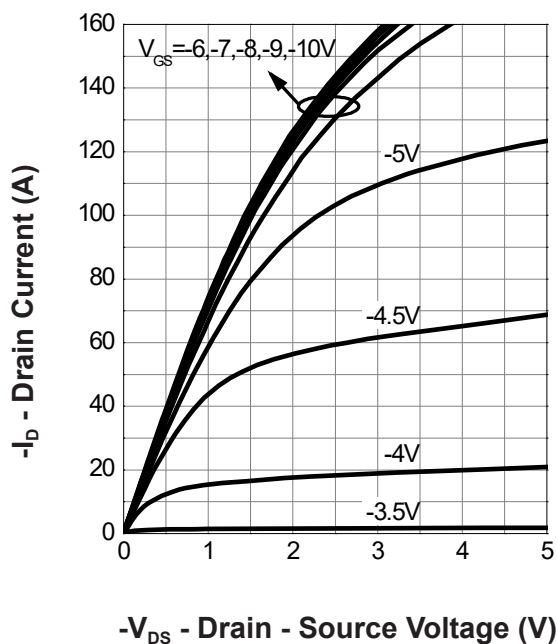
Safe Operation Area



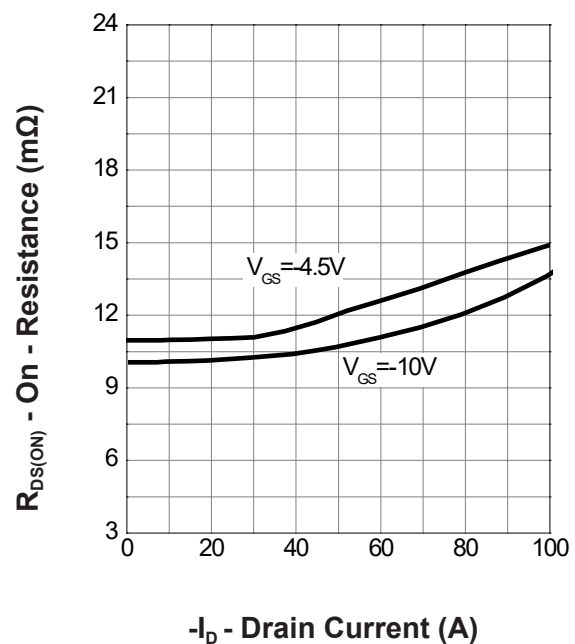
Thermal Transient Impedance



Output Characteristics

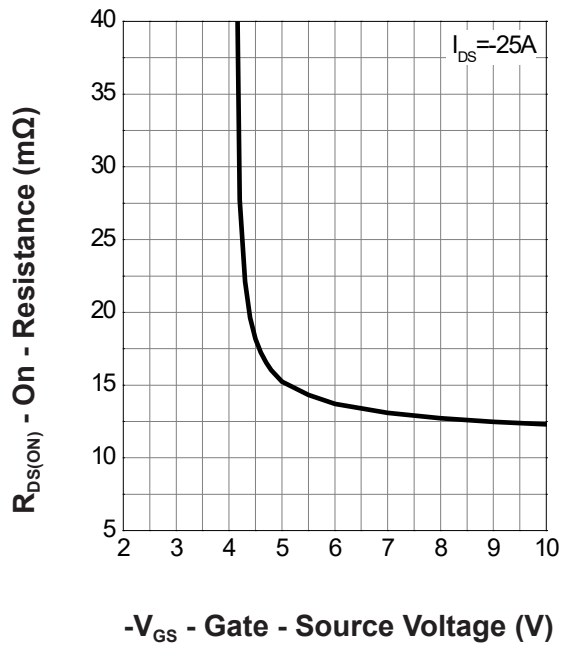


Drain-Source On Resistance

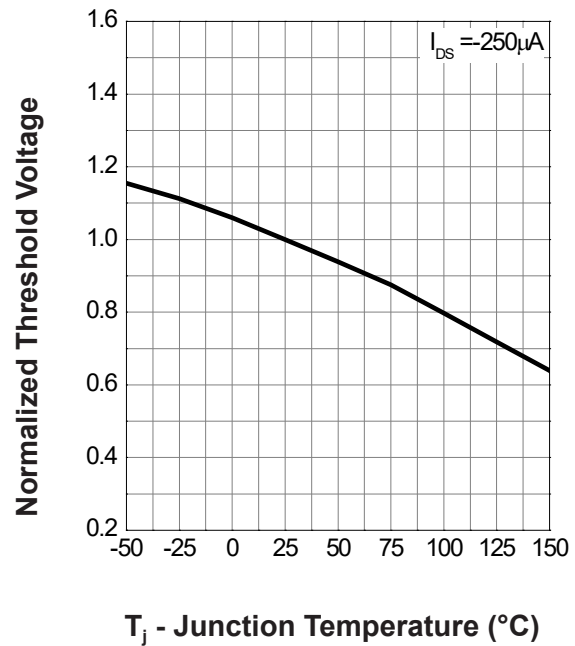


Typical Operating Characteristics(Cont.)

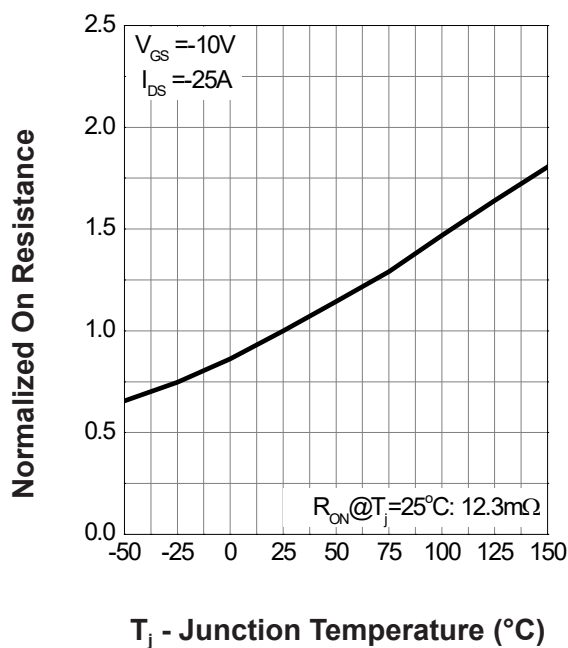
Gate-Source On Resistance



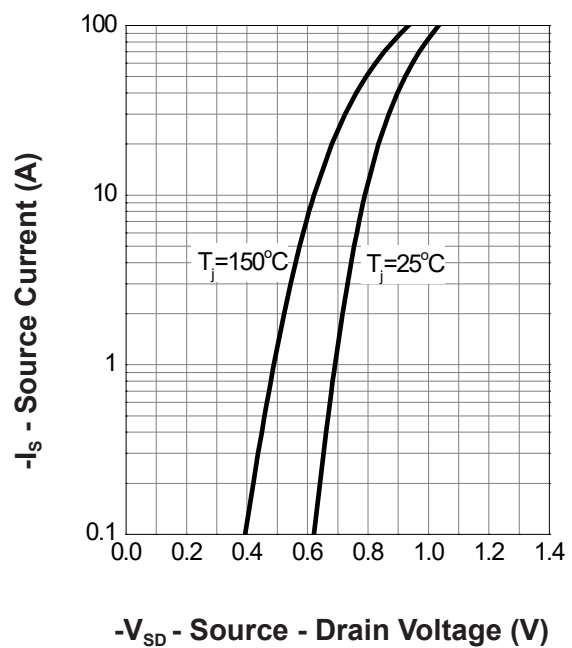
Gate Threshold Voltage



Drain-Source On Resistance

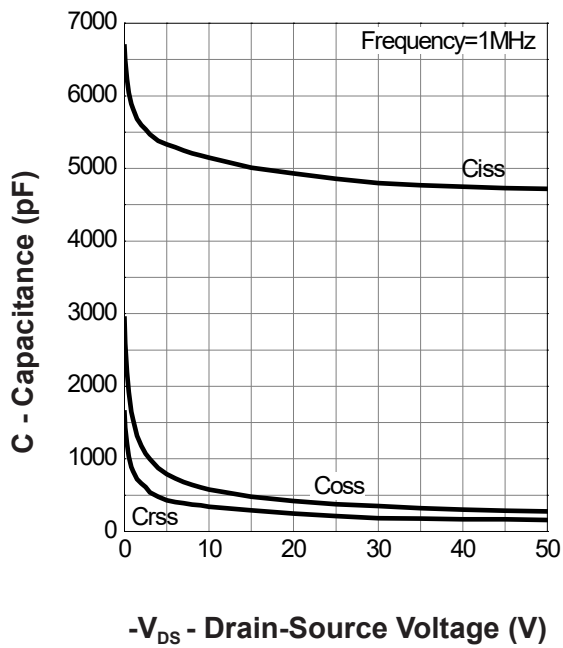


Source-Drain Diode Forward

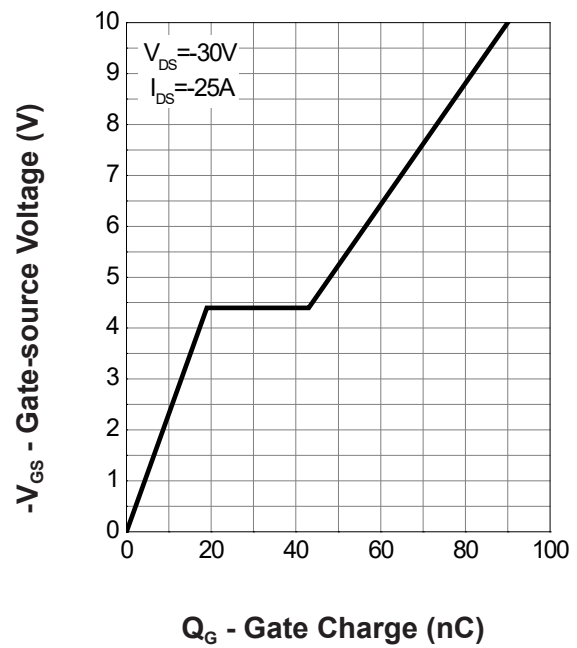


Typical Operating Characteristics(Cont.)

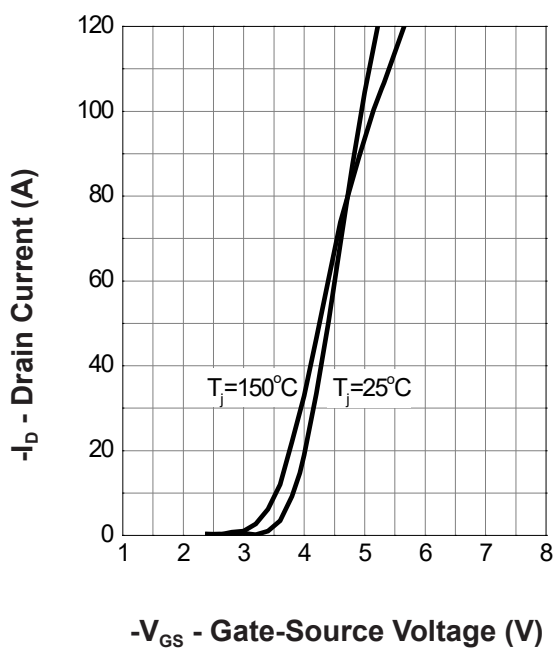
Capacitance



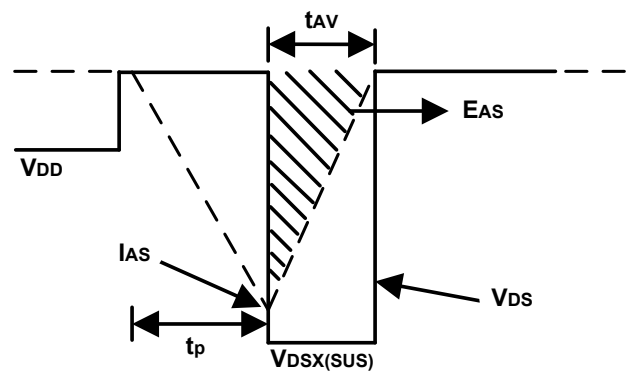
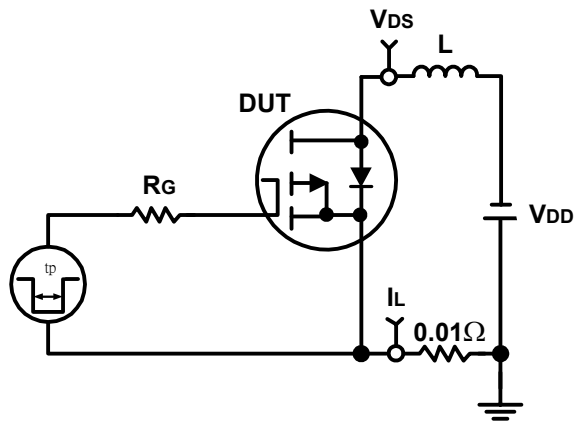
Gate Charge



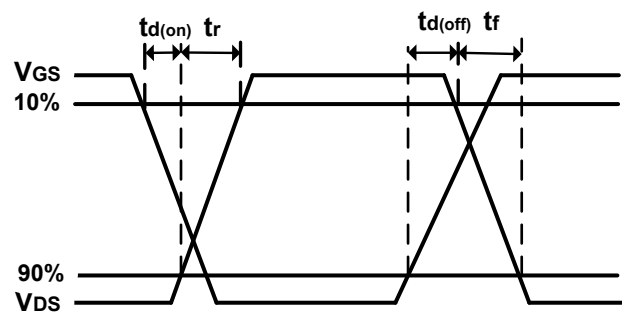
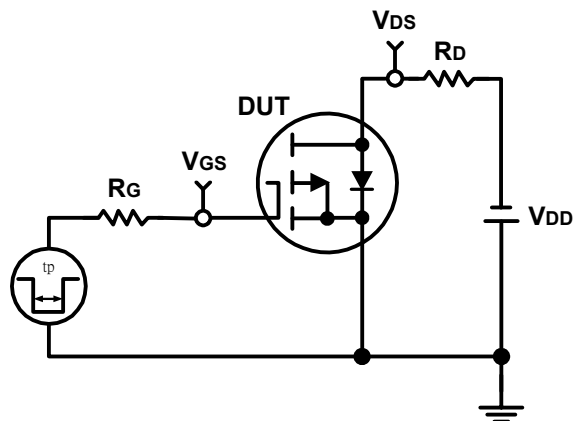
Transfer Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Package Information

DFN5X6 OUTLINE

